

ABSTRACT OF THE DISCLOSURE

A semiconductor device has a MOSFET. The MOSFET includes source and drain regions, a gate insulating film, a gate electrode, and first, second, and third metal silicide films. The source and drain regions are formed in the major surface region of a semiconductor substrate. The gate insulating film is formed on the channel region between the source and drain regions. The gate electrode is formed on the gate insulating film and includes a poly-Si_{1-x}Ge_x layer having a Ge/(Si+Ge) composition ratio \underline{x} ($0 < x < 0.2$). The first metal silicide film is formed on the gate electrode and made of NiSi_{1-y}Ge_y. The second and third metal silicide films are formed on the source and drain regions, respectively, and made of NiSi.